



**Product data sheet** 

### 1. General description

Hyperfast power diode in a 2-lead IITO220 plastic package.

### 2. Features and benefits

- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

### 3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

### 4. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	00		V
$I_{F(AV)}$	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 90 °C; square-wave pulse Fig. 1; Fig. 2; Fig. 3	30			A	
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 90 °C; square-wave pulse	60			A	
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; <u>Fig. 4</u>	200			A	
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		2	20		А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	- 1.38 1.8		V		
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 7$		-	-	35	ns

## 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	A	anode		К <u>— Д</u> А 001ааа020
mb	n.c.	mounting base; isolated		001aaa020
			U U	
			1 2 IITO220-2L	

## 6. Ordering information

Table 3. Ordering information								
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYC30Y-600P	IITO220-2L	BYC30Y-600PQ	Tube	50	IITO220E-2L	03-Mar-2020		

### 7. Marking

Table 4. Marking codes	
Type number	Marking codes
BYC30Y-600P	BYC30Y 600P

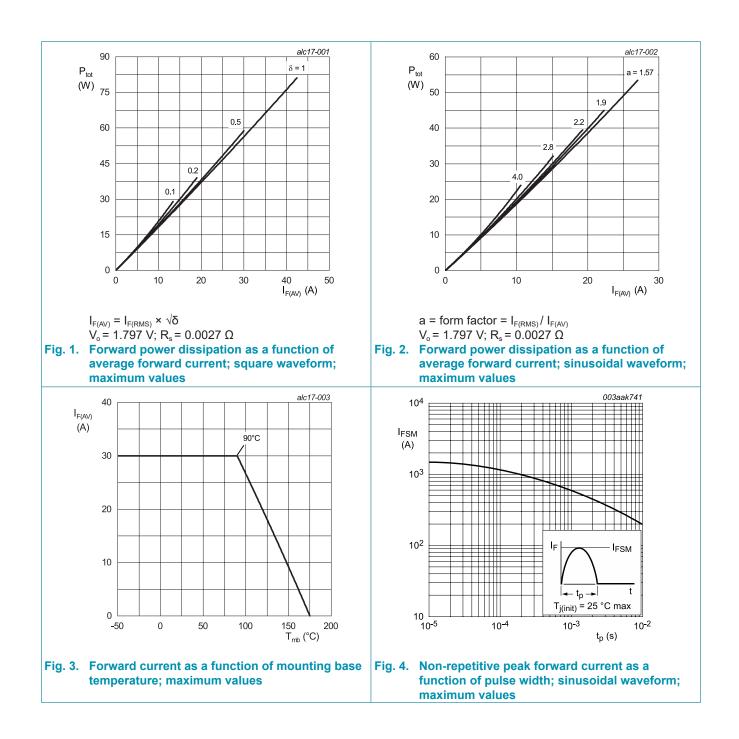
## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

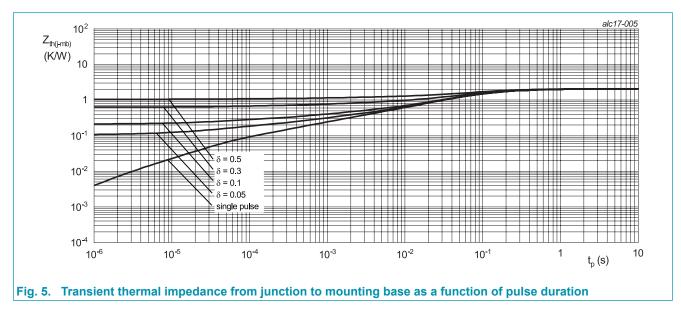
Symbol	Parameter	Conditions	Values	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
V <sub>R</sub>	reverse voltage	DC	600	V
$I_{\rm F(AV)}$	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 90 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	30	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 90 °C; square-wave pulse	60	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; Fig. 4	200	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C

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### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2.1	K/W
$R_{\text{th}(j\text{-}a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

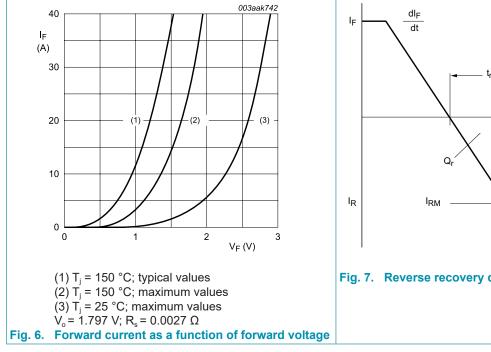


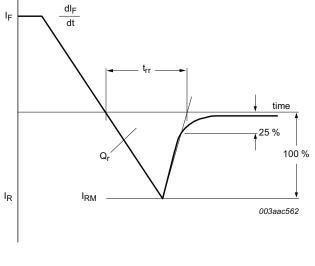
## **10. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	рF

### **11. Characteristics**

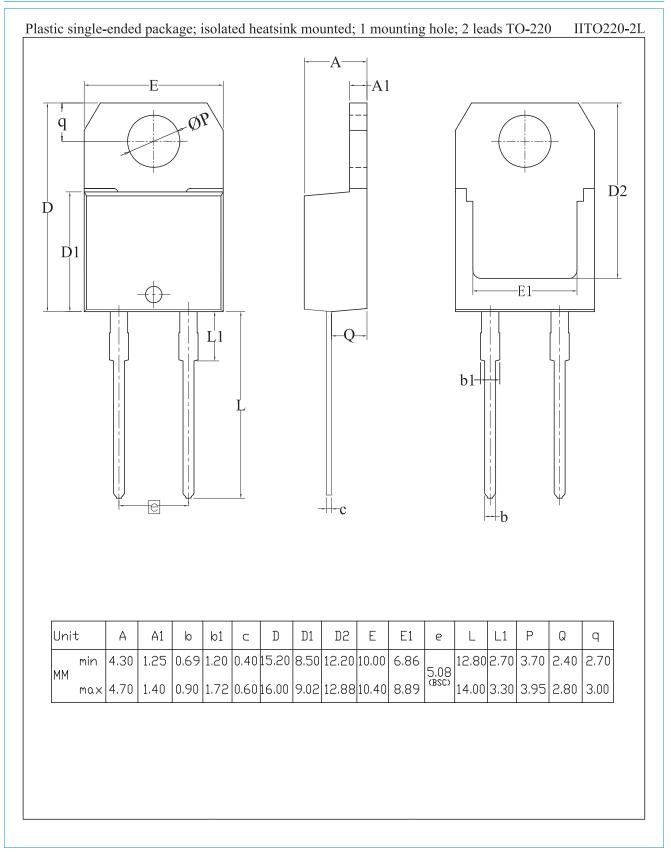
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics	· · · · · · · · · · · · · · · · · · ·				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	1	mA
Dynamic	characteristics	· · · · · · · · · · · · · · · · · · ·				
Q <sub>r</sub> recovered	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/$ µs; $T_J = 25 \text{ °C}; Fig. 7$	-	50	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; \text{ Fig. 7}$	-	280	-	nC
t <sub>rr</sub> reverse recovery tim	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	-	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	35	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	3.5	-	A
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 125 °C; <u>Fig. 7</u>	-	7.6	-	А





### Fig. 7. Reverse recovery definitions; ramp recovery

### 12. Package outline



# BYC30Y-600P

### Hyperfast power diode

### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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